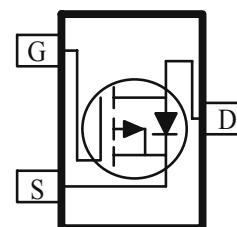
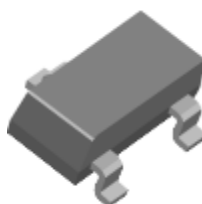


P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (OHM)	I _D (A)
-20	0.055 @ V _{GS} = -4.5V	-3.6
	0.089 @ V _{GS} = -2.5V	-2.8
	0.20 @ V _{GS} = -1.8V	-1.8

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Ratings	Units
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±12	
Continuous Drain Current ^a	I _D	T _A =25°C	-3.6
		T _A =70°C	-2.9
Pulsed Drain Current ^b	I _{DM}	-10	A
Continuous Source Current (Diode Conduction) ^a	I _S	±0.46	A
Power Dissipation ^a	P _D	T _A =25°C	1.25
		T _A =70°C	0.8
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	R _{THJA}	t ≤ 5 sec	100
		Steady-State	166

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.7			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			-10	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10			A
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -3.6 \text{ A}$			55	mΩ
		$V_{GS} = -2.5 \text{ V}, I_D = -2.8 \text{ A}$			89	
		$V_{GS} = -1.8 \text{ V}, I_D = -1.8 \text{ A}$			200	
Forward Transconductance ^A	g_{fs}	$V_{DS} = -5 \text{ V}, I_D = -3.6 \text{ A}$		12		S
Diode Forward Voltage	V_{SD}	$I_S = -0.46 \text{ A}, V_{GS} = 0 \text{ V}$		-0.60		V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -3.6 \text{ A}$		16.7		nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			1.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, I_L = -1 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_G = 6 \Omega$		9		ns
Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			25		
Fall-Time	t_f			20		

Notes

- Pulse test: $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics

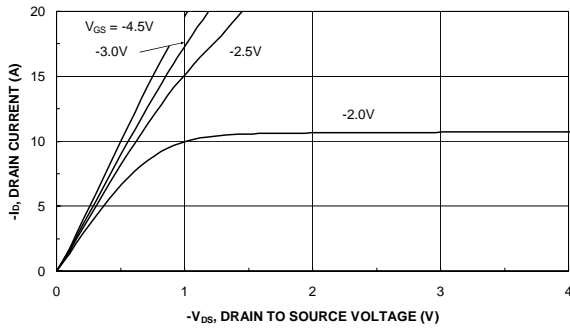


Figure 1. Output Characteristics

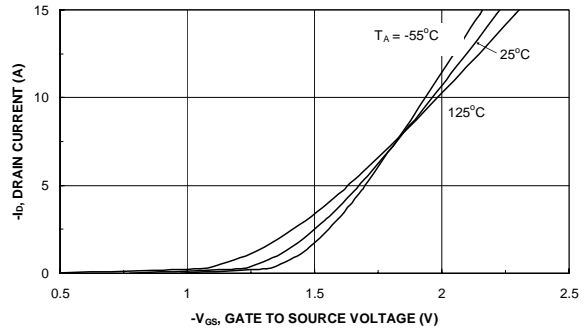


Figure 2. Transfer Characteristics

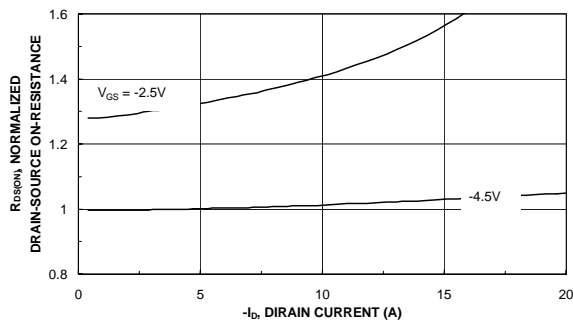


Figure 3. On-Resistance vs. Drain Current

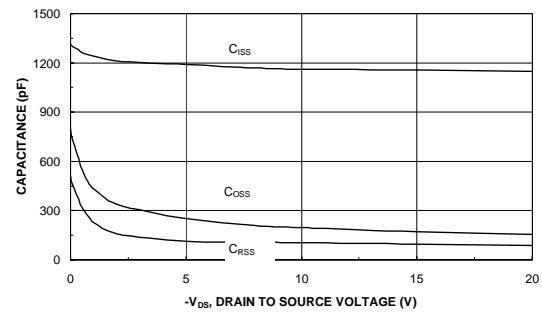


Figure 4. Capacitance

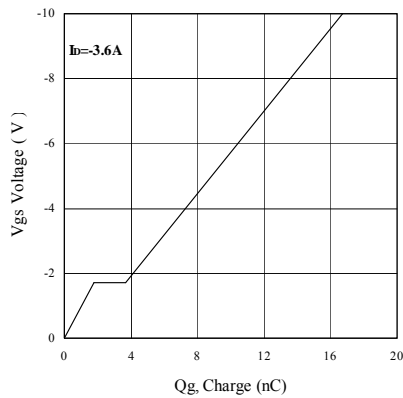


Figure 5. Gate Charge

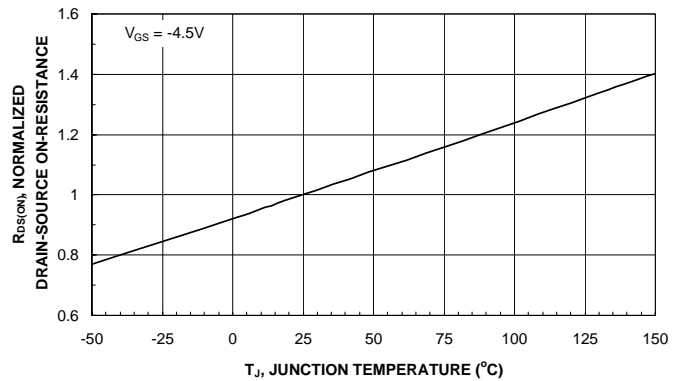


Figure 6. On-Resistance vs. Junction Temperature

Typical Electrical Characteristics

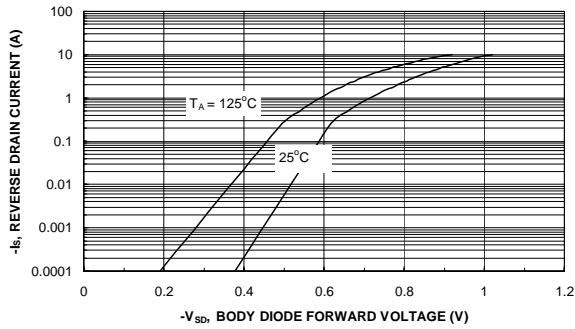


Figure 7. Source-Drain Diode Forward Voltage

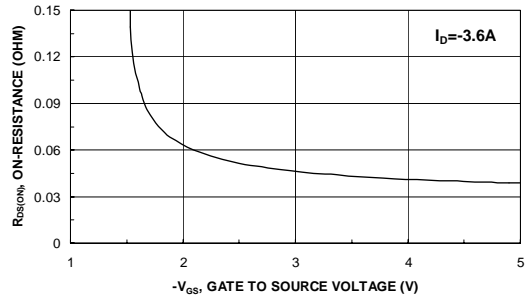


Figure 8. On-Resistance with Gate to Source Voltage

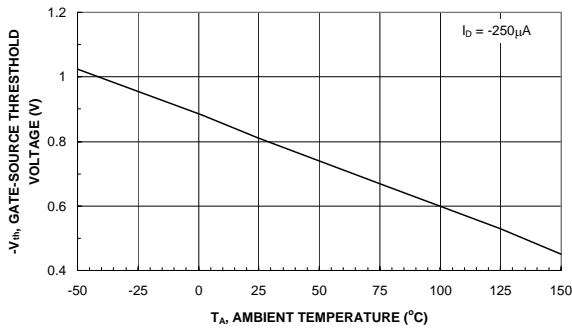


Figure 9. Vth Gate to Source Voltage Vs Temperature

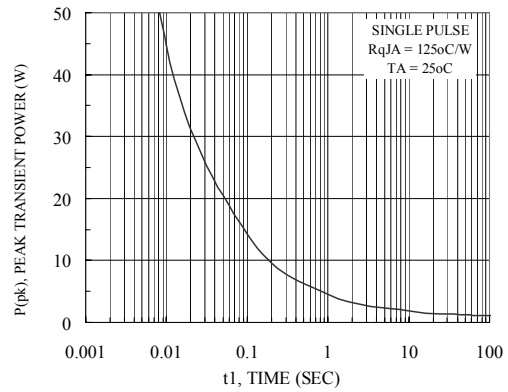


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

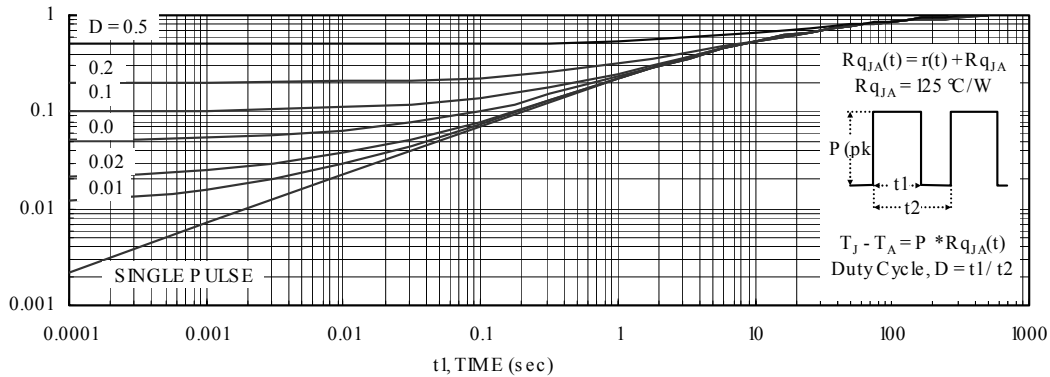
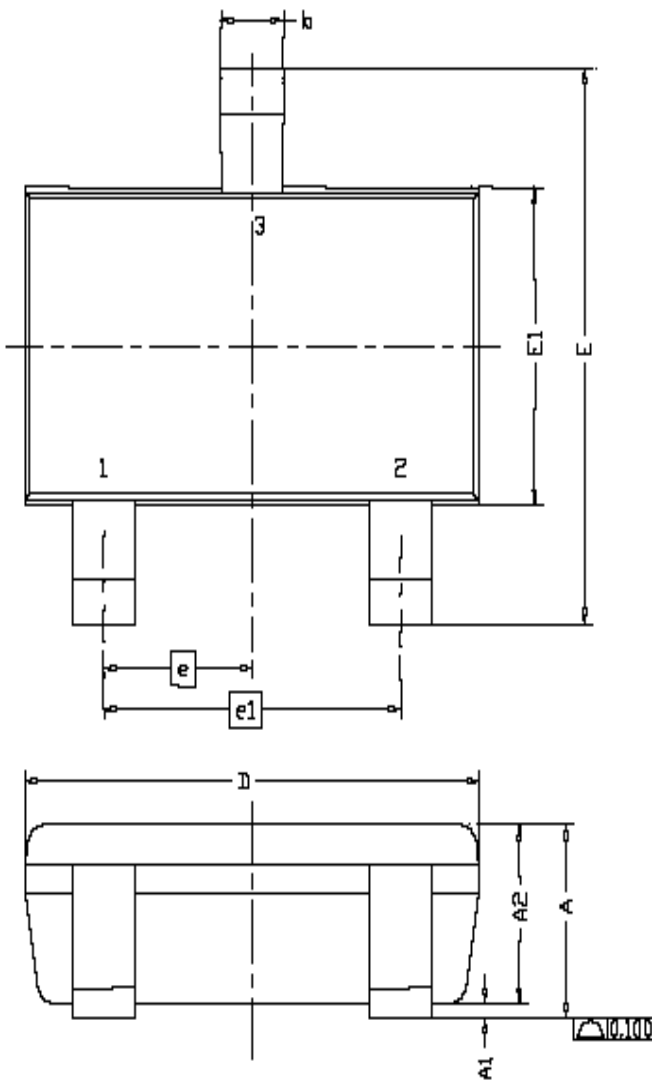


Figure 11. Transient Thermal Response Curve

Ordering information

- AM2325P-T1-XX
 - A: Analog Power
 - M: MOSFET
 - 2325: Part number
 - P: P-Channel
 - T1: Tape & reel
 - XX: Blank: Standard
PF: Lead-free

Package Information



DIM.	MILLIMETERS		
	MIN	NOM	MAX
A	0.935	0.95	1.10
A1	0.01	---	0.10
A2	0.85	0.90	0.925
b	0.30	0.40	0.50
c	0.10	0.15	0.25
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.60
L1	0.60REF		
L2	0.25BSC		
R	0.10	---	---
θ	0°	4°	8°
θ_1	7°NOM		

